

V_{DSS}	80V
$R_{DS(on)}(Max.)$	130m Ω
I_D	$\pm 3.4A$
P_D	2.0W

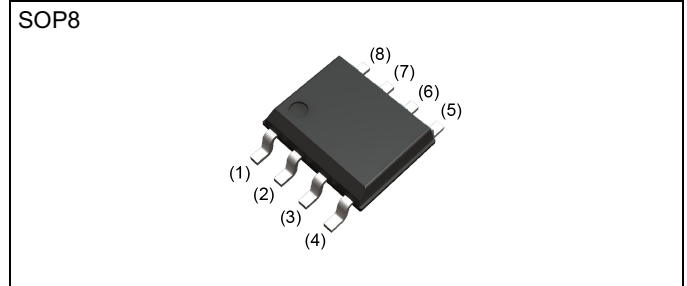
●Features

- 1) Low on - resistance.
- 2) Small Surface Mount Package .
- 3) Pb-free lead plating ; RoHS compliant.
- 4) Halogen Free.

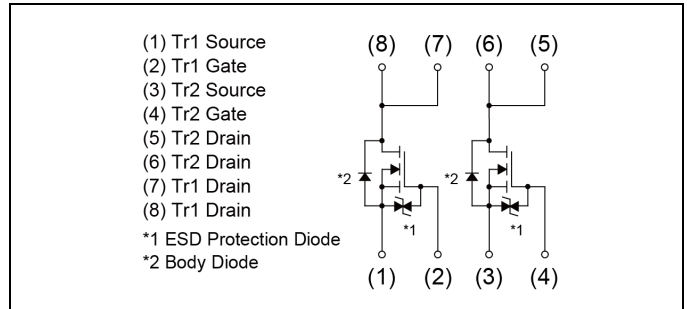
●Application

Switching

●Outline



●Inner circuit



●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	330
Tape width (mm)	12	
Basic ordering unit (pcs)	2500	
Taping code	TB	
Marking	SH8K41	

●Absolute maximum ratings ($T_a = 25^\circ C$) <It is the same ratings for the Tr1 and Tr2>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	80	V
Continuous drain current	I_D^{*1}	± 3.4	A
Pulsed drain current	$I_{D,pulse}^{*2}$	± 13.6	A
Gate - Source voltage	V_{GSS}	± 20	V
Avalanche energy, single pulse	E_{AS}^{*3}	8.4	mJ
Avalanche current	I_{AS}^{*3}	3.4	A
Power dissipation	total	P_D^{*4}	2.0
	element	P_D^{*4}	1.4
Junction temperature	T_j	150	$^\circ C$
Range of storage temperature	T_{stg}	-55 to +150	$^\circ C$

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*4}	-	62.5	-	°C/W

● Electrical characteristics ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	80	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	81.3	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	-4.4	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3.4A$	-	90	130	mΩ
		$V_{GS} = 4.5V, I_D = 3.4A$	-	110	150	
		$V_{GS} = 4.0V, I_D = 3.4A$	-	120	160	
Transconductance	g_{fs}^{*5}	$V_{DS} = 10V, I_D = 3.4A$	3.0	-	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 $L \approx 1\text{mH}$, $V_{DD} = 40V$, $R_G = 25\Omega$, STARTING $T_{ch} = 25^\circ\text{C}$ Fig.3-1,3-2

*4 Mounted on a ceramic board.

*5 Pulsed

● **Electrical characteristics** ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	600	-	pF
Output capacitance	C_{oss}	$V_{DS} = 10V$	-	100	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	40	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 40V, V_{GS} = 10V$	-	12	-	ns
Rise time	t_r^{*5}	$I_D = 1.7A$	-	15	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 24\Omega$	-	40	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	12	-	

● **Gate charge characteristics** ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 40V, I_D = 3.4A$ $V_{GS} = 5.0V$	-	6.6	-	nC
Gate - Source charge	Q_{gs}^{*5}		-	1.8	-	
Gate - Drain charge	Q_{gd}^{*5}		-	2.2	-	

● **Body diode electrical characteristics** (Source-Drain) ($T_a = 25^\circ\text{C}$)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I_S^{*1}	$T_a = 25^\circ\text{C}$	-	-	1.6	A
Body diode pulse current	I_{SP}^{*2}		-	-	13.6	
Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 1.6A$	-	-	1.2	V

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve



Fig.2 Maximum Safe Operating Area

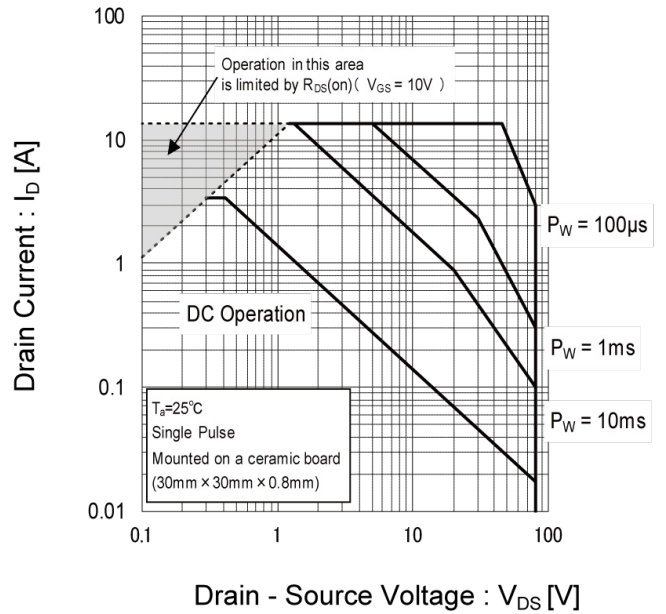


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

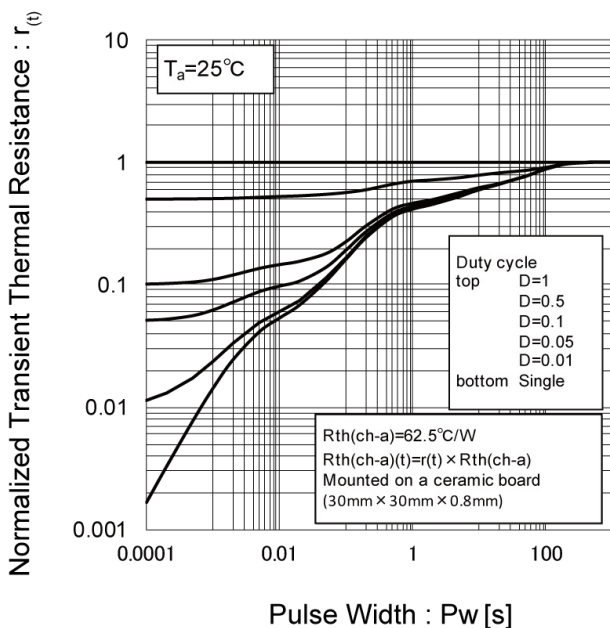
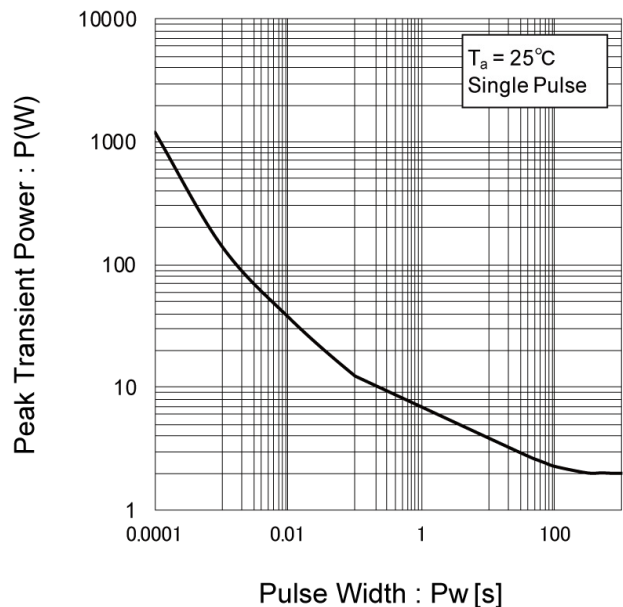


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

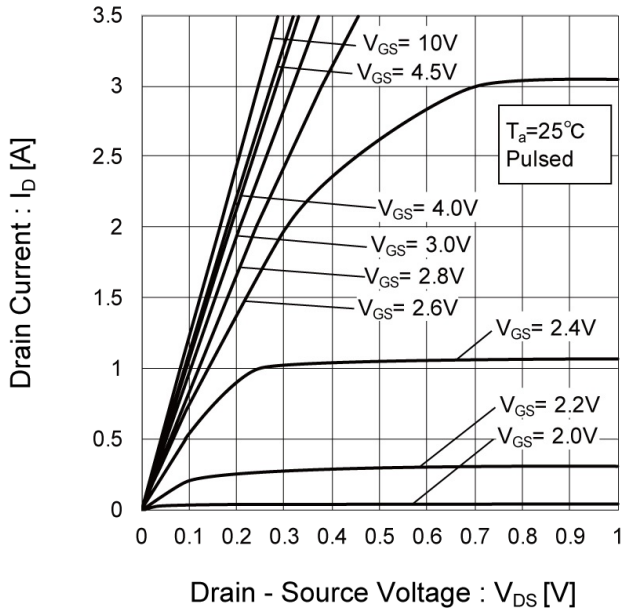


Fig.6 Typical Output Characteristics(II)

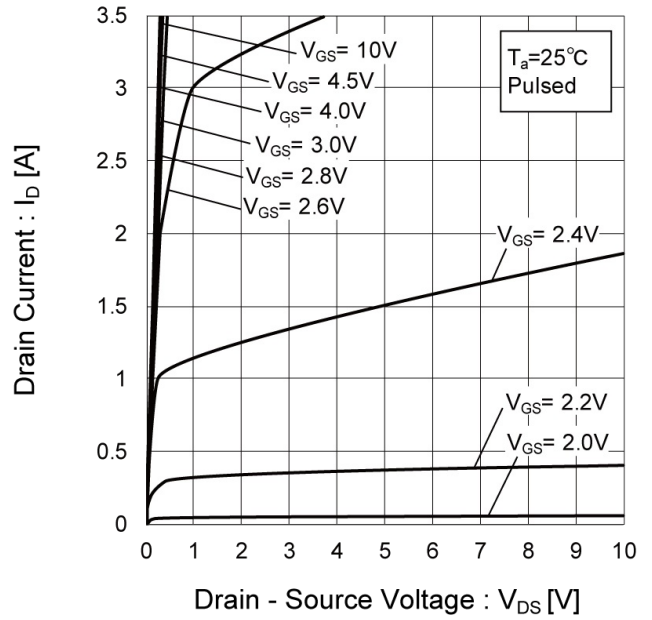
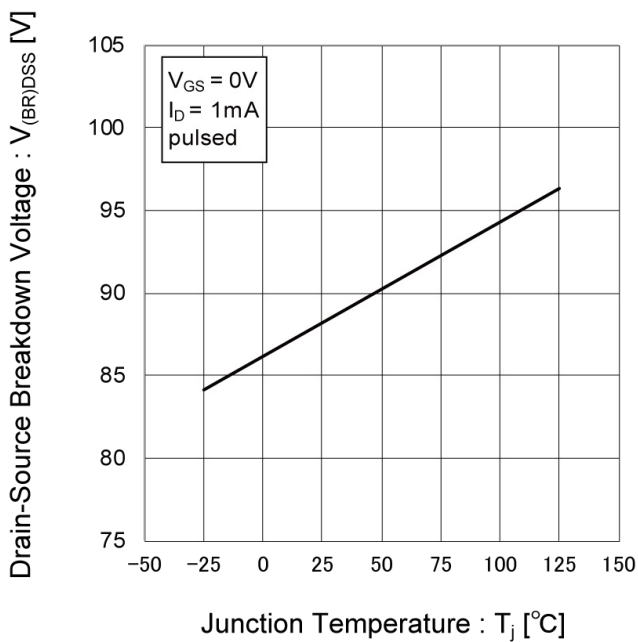


Fig.7 Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

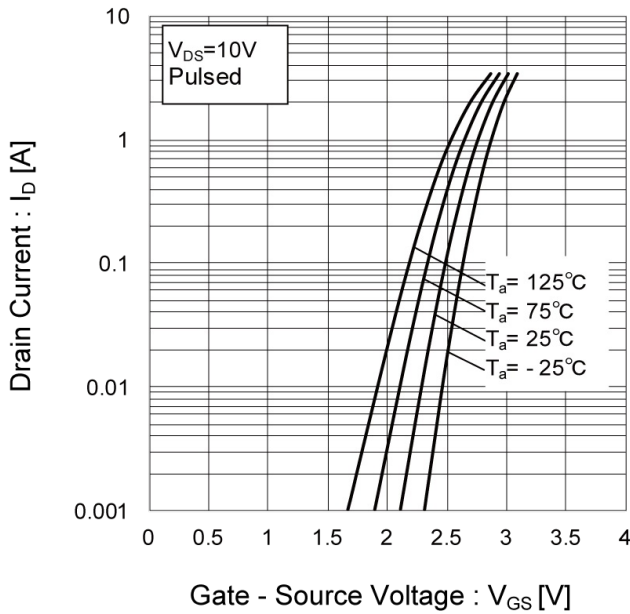


Fig.9 Gate Threshold Voltage vs. Junction Temperature

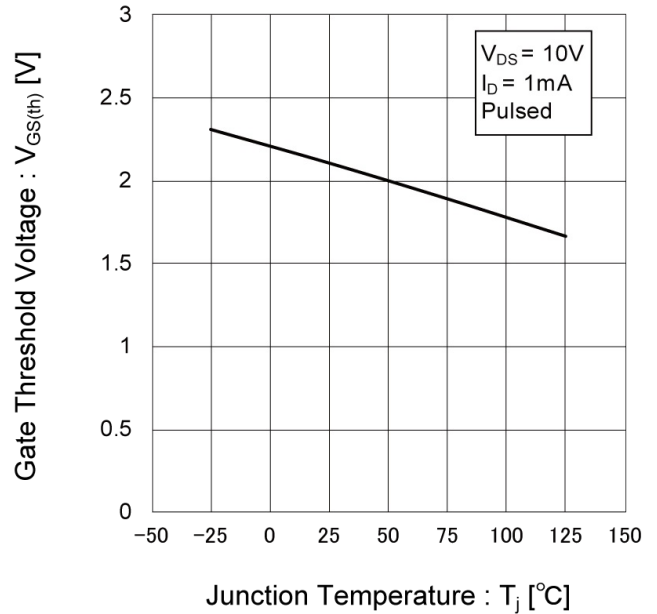
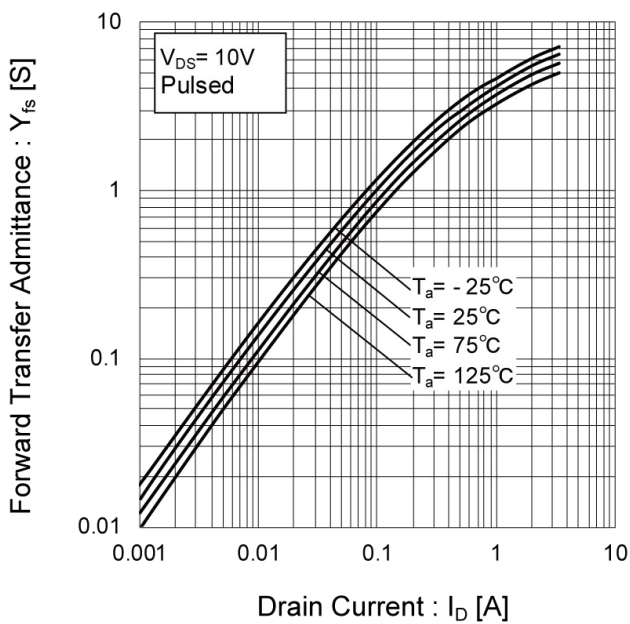


Fig.10 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.11 Drain Current Derating Curve



Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

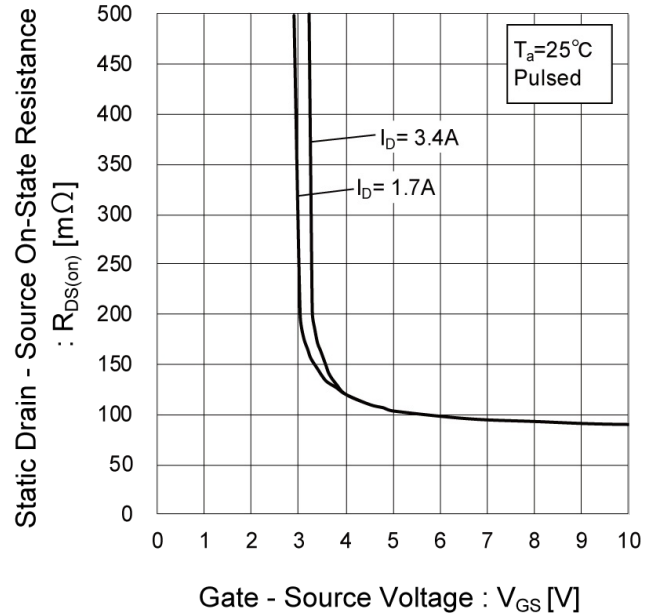
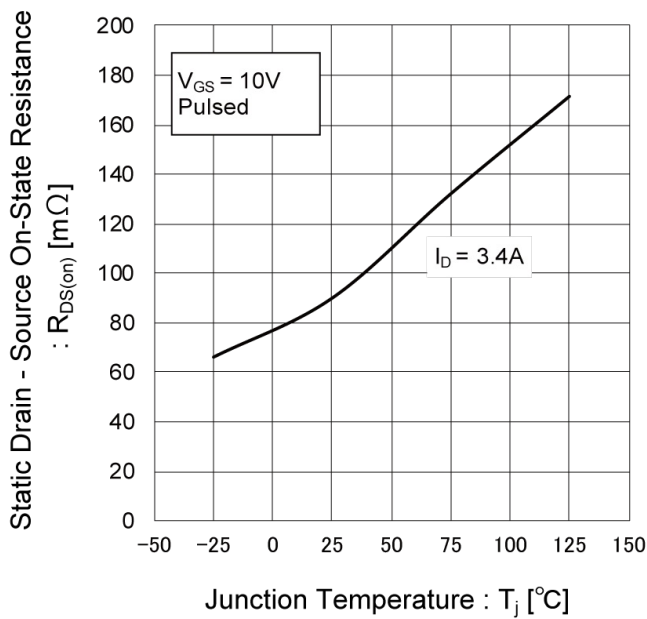


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

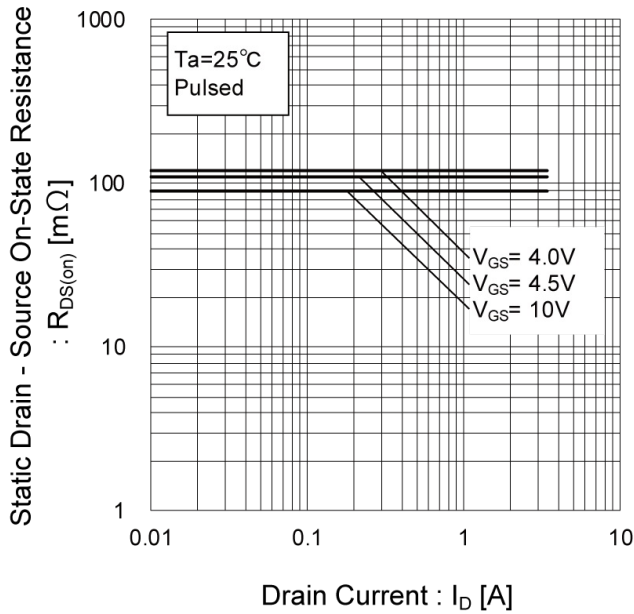


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

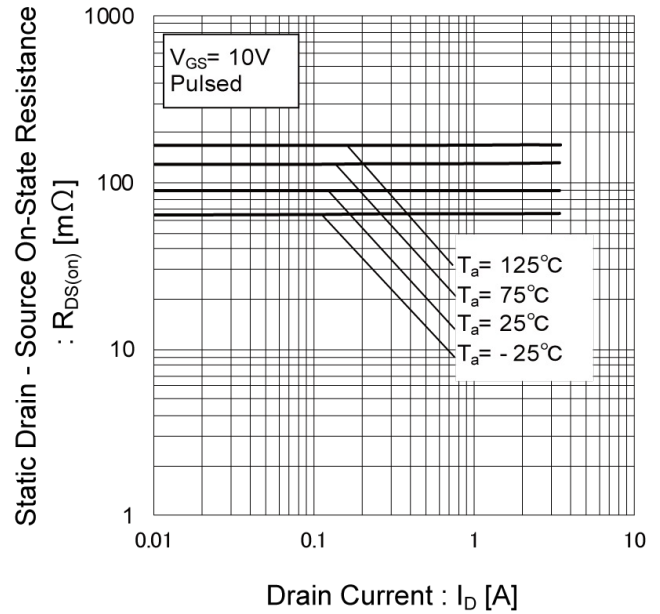


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

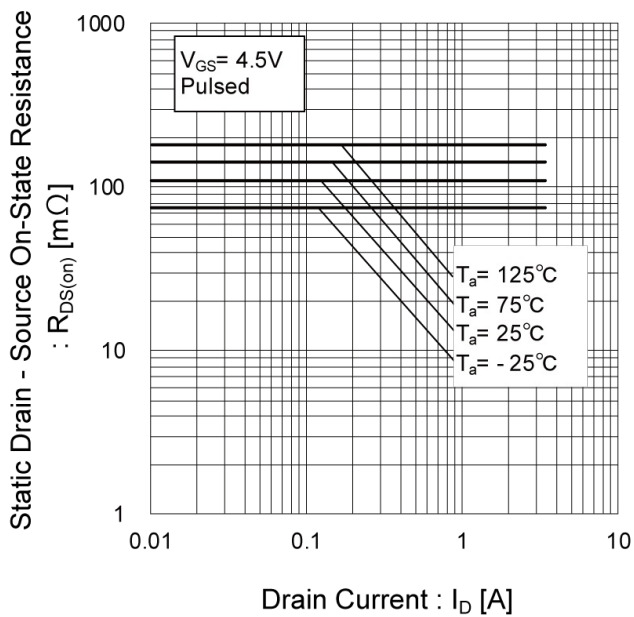
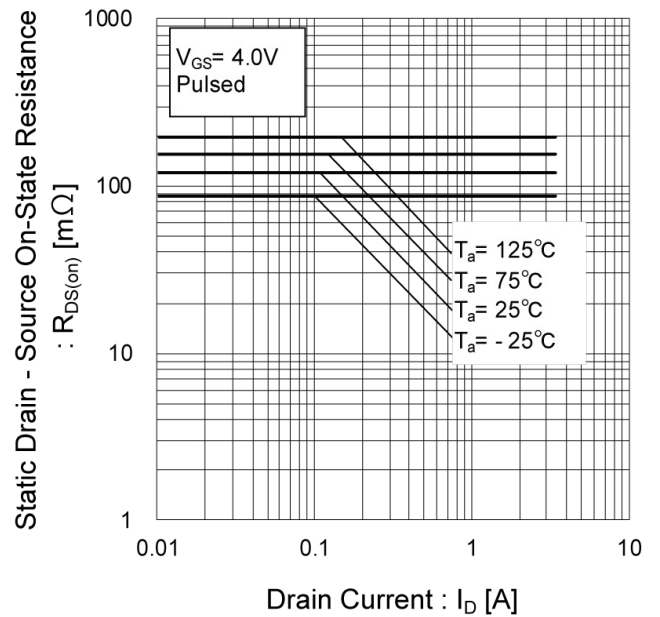


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)



● Electrical characteristic curves

Fig.18 Typical Capacitance vs. Drain - Source Voltage

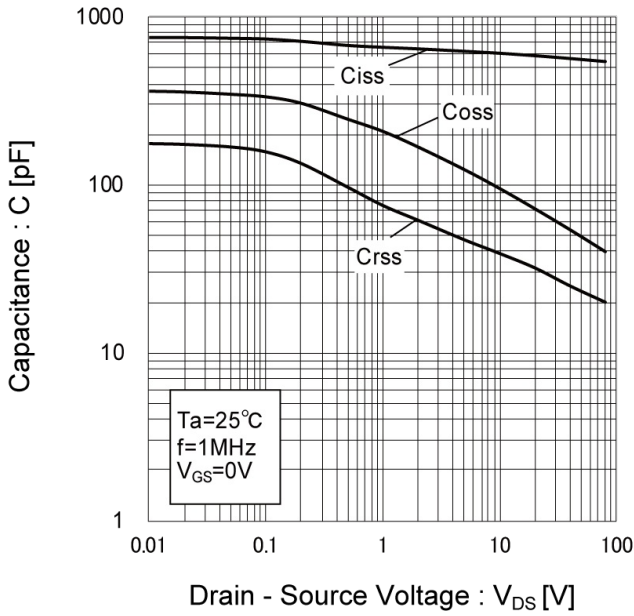


Fig.19 Switching Characteristics

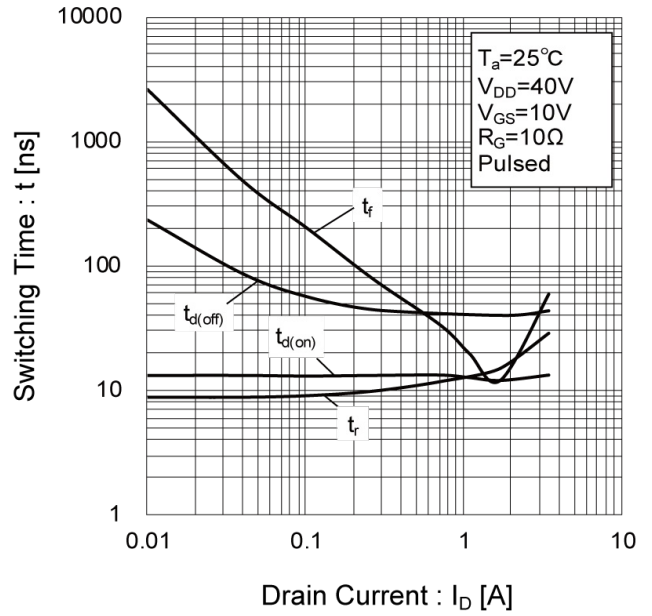


Fig.20 Dynamic Input Characteristics

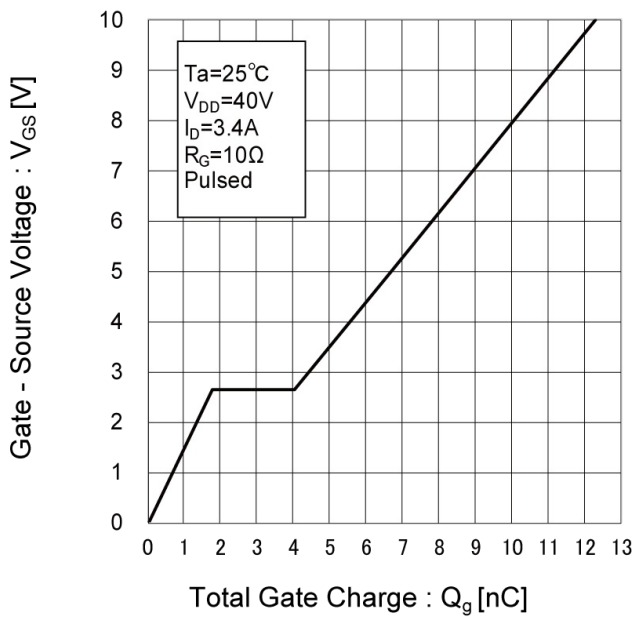
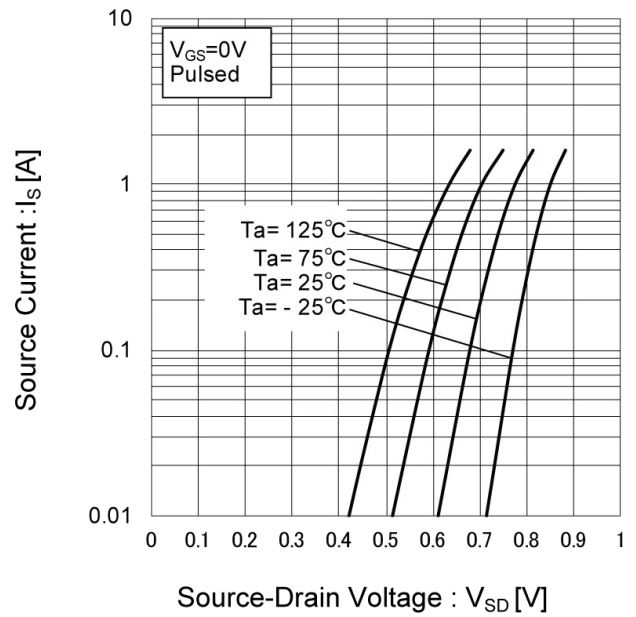


Fig.21 Source Current vs. Source Drain Voltage



● Measurement circuits <It is the same for the Tr1 and Tr2>

Fig.1-1 Switching Time Measurement Circuit

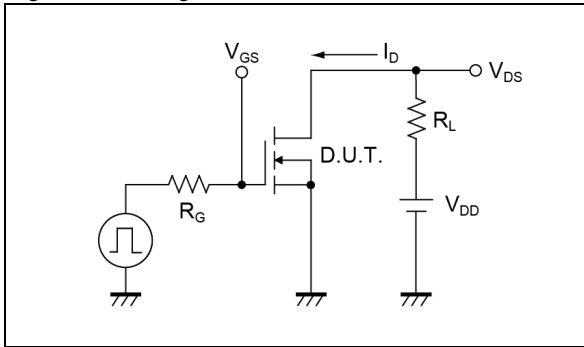


Fig.1-2 Switching Waveforms

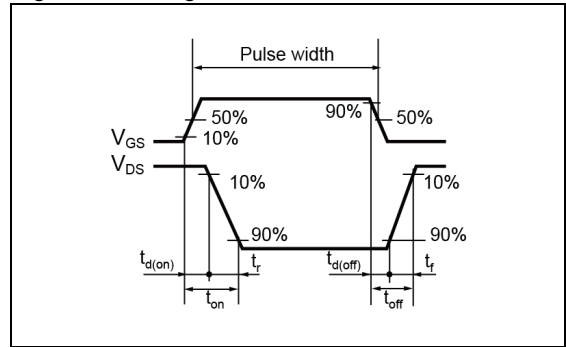


Fig.2-1 Gate Charge Measurement Circuit

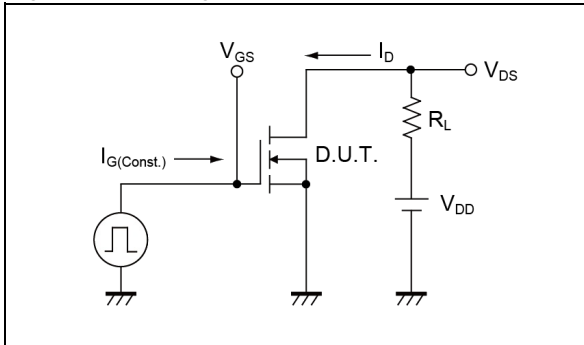


Fig.2-2 Gate Charge Waveform

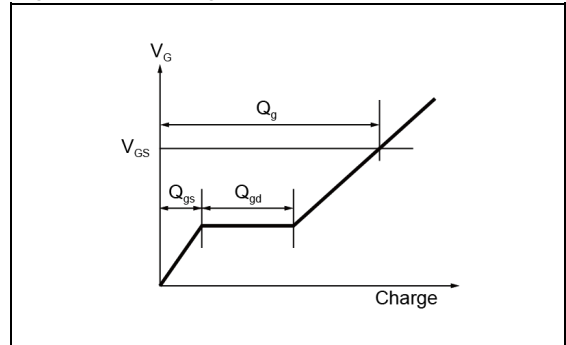


Fig.3-1 Avalanche Measurement Circuit

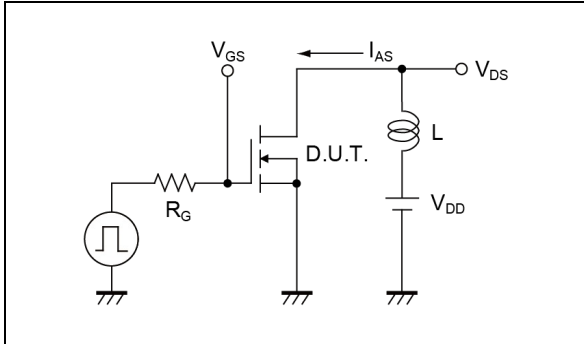
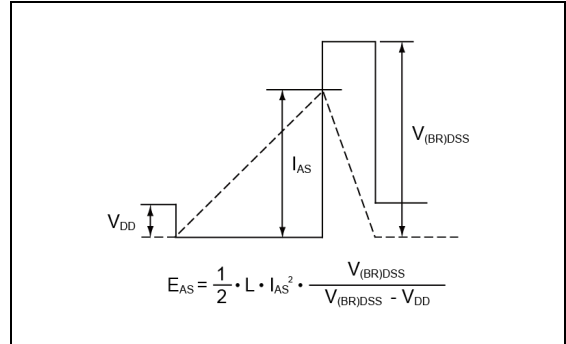
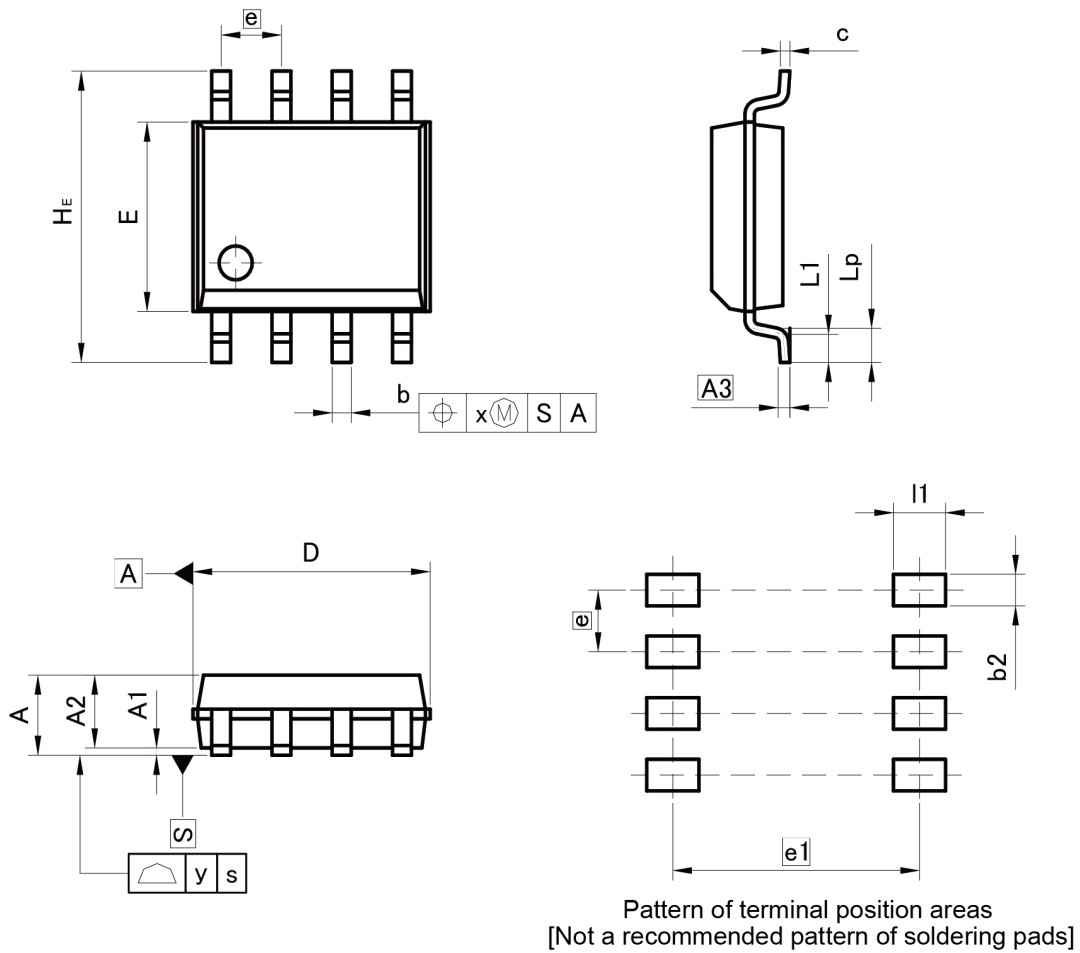


Fig.3-2 Avalanche Waveform



●Dimensions

SOP8



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.15		0.006	
A2	1.40	1.60	0.055	0.063
A3	0.25		0.010	
b	0.30	0.50	0.012	0.020
c	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
e	1.27		0.050	
HE	5.70	6.30	0.224	0.248
L1	0.50	0.70	0.020	0.028
Lp	0.65	0.85	0.026	0.033
x	0.15		0.006	
y	0.10		0.004	

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.65	-	0.026
e1	5.15		0.203	
l1	-	1.15	-	0.045

Dimension in mm/inches

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